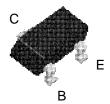


# FSB660 / FSB660A



SuperSOT<sup>™</sup>-3 (SOT-23)

# **PNP Low Saturation Transistor**

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous.

# **Absolute Maximum Ratings\*** T<sub>A = 25°C unless otherwise noted</sub>

Symbol	Parameter	FSB660/FSB660A	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	2	Α
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics \_\_\_\_\_ T\_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FSB660/FSB660A	
P <sub>D</sub>	Total Device Dissipation	500	mW
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	250	°C/W

# **PNP Low Saturation Transistor**

(continued)

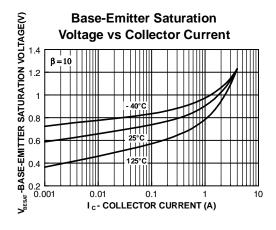
# **Electrical Characteristics**

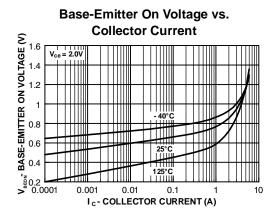
 $T_{A=25^{\circ}\text{C}}$  unless otherwise noted

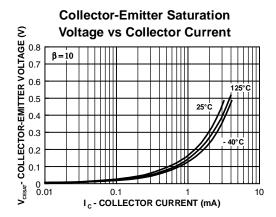
Symbol	Parameter Test Conditions			Max	Units
OFF CHAI	RACTERISTICS				
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA	60		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 100 μA	60		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100 μA	5		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30 V V <sub>CB</sub> = 30 V, T <sub>A</sub> =100°C		100 10	nA uA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V		100	nA
ON CHAR	ACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 2 V	70		-
		I <sub>C</sub> =500mA, V <sub>CE</sub> =2V <b>FSB660</b>	100	300	
		FSB660A	250	550	
		I <sub>C</sub> = 1 A, V <sub>CE</sub> = 2 V	80		
		I <sub>C</sub> = 2 A, V <sub>CE</sub> = 2 V	40		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA		300	mV
-()		I <sub>C</sub> = 2 A, I <sub>B</sub> =200 mA <b>FSB660</b>		350	
		FSB660A		300	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA		1.25	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1 A, V <sub>CE</sub> = 2 V		1	V
SMALL SI	GNAL CHARACTERISTICS				
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1MHz		30	pF
f <sub>T</sub>	Transition Frequency	I <sub>C</sub> = 100 mA,V <sub>CE</sub> = 5 V, f=100MHz	75		-

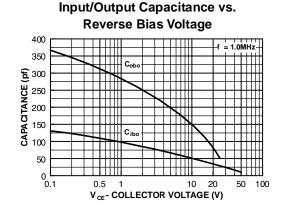
\*Pulse Test: Pulse Width  $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$ 

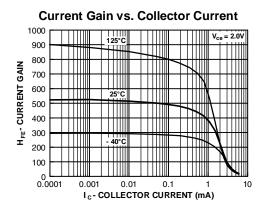
# **Typical Characteristics**

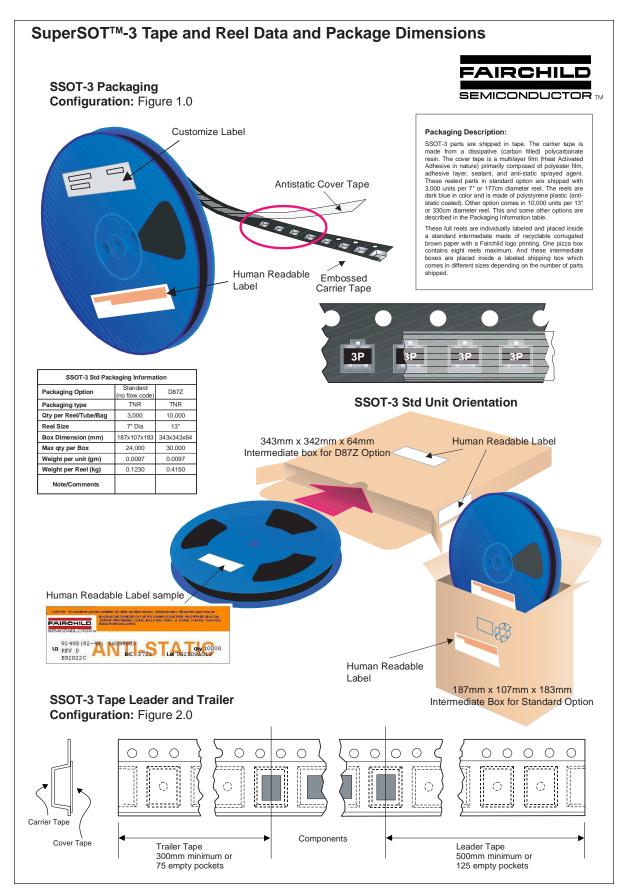


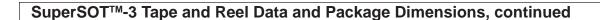






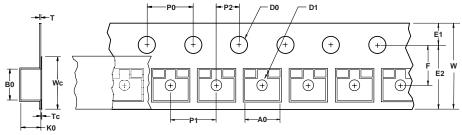






### **SSOT-3 Embossed Carrier Tape**

Configuration: Figure 3.0



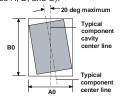


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

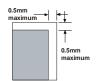
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



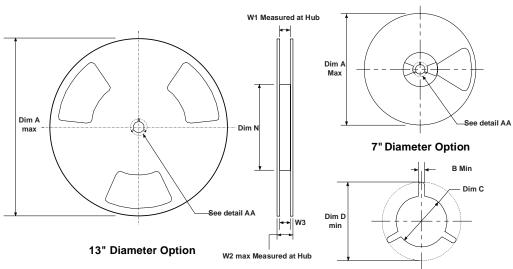
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

DETAIL AA

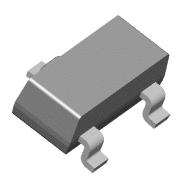
# **SSOT-3 Reel Configuration:** Figure 4.0

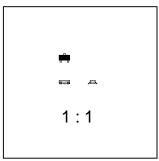


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

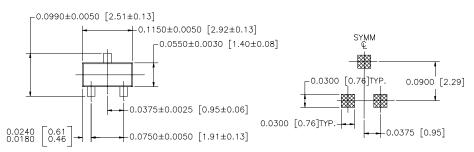
# SuperSOT™-3 (FS PKG Code 32)



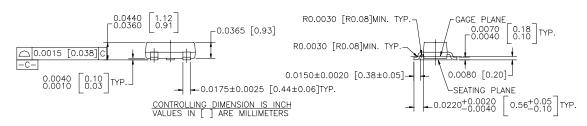


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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